

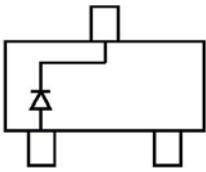
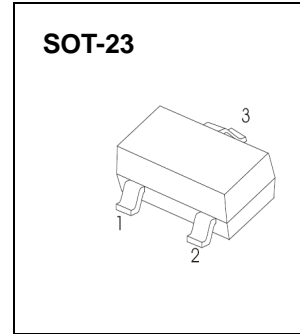


DONGGUAN NANJING ELECTRONICS LTD.,
SOT-23 Plastic-Encapsulate Diodes

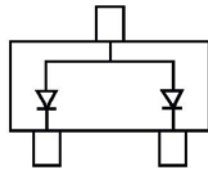
BAS40/-04/-05/-06 SCHOTTKY BARRIER DIODE

FEATURES

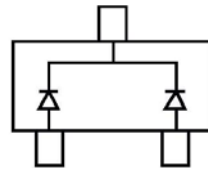
- Low Forward Voltage
- Fast Switching



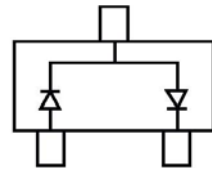
BAS40 MARKING: 43•



BAS40-06 MARKING: 46



BAS40-05 MARKING: 45



BAS40-04 MARKING: 44

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	V_{RRM}	40	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
Forward continuous current	I_{FM}	200	mA
Power dissipation	P_D	200	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	500	°C/W
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Diode capacitance	C_D	$V_R = 0, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_r = 1mA, I_R = I_F = 10mA$ $R_L = 100\Omega$		5	ns

Typical Characteristics

BAS40/-04/-05/-06

